Author's Accepted Manuscript

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PII: S0039-6028(17)30088-2

DOI: http://dx.doi.org/10.1016/j.susc.2017.04.005

Reference: SUSC21016

To appear in: Surface Science

Received date: 1 February 2017 Revised date: 8 April 2017 Accepted date: 10 April 2017

Cite this article as: H. Ueba, Analysis of reaction rates of single molecules of metal surfaces, *Surface Science*, http://dx.doi.org/10.1016/j.susc.2017.04.005

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Analysis of reaction rates of single molecules on metal surfaces

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(Dated: April 12, 2017)

Abstract

The experimental results of the action spectra i.e., @reaction rate R(V) as a function of a bias voltage V are analyzed for rotation of a single CCH (D) molecule on a Cu (100) surface [L. Lauhon and W. Ho, Surf. Sci. 451, 291 (2000)] and hopping of a single H(D)₂O molecule on Pd(111) surface [Fomin et al, Surf. Sci. 600, 542 (2006)]. In the former system it is identified that rotation occurs if enough energy stored in the C-H (D) in-plane bending (IPB) mode excited by tunneling electron is transferred to the C-H (D) out of plane bending (OPB) mode (reaction coordinate mode) via the anharmonic mode coupling in a single electron process. The calculated R(V) shows an excellent agreement with the experimental results except at the low bias voltages below $V \simeq 60 \text{ mV}$ where no experimental data is available for the nonlinear current I dependence of R(I). A reproduction of the experimental R(V) at the higher voltage region allows us to determine the vibrational density of states of the C-H IPB mode and its coupling rate to the C-H (D) OPB mode as well as the inelastic tunneling current to excite IPB mode. A change of a conductance upon excitation of the C-H IPB mode enables us to evaluate the electron-vibration coupling strength inducing the rotation motion of CCH molecule. In the latter system investigated at a high temperature of about 40 K, the constant R(V) due to thermal hopping followed by the rapid increase is satisfactory explained by anharmonic inter-mode coupling between the scissor mode excited by tunneling electrons and the frustrated translation mode for $H(D)_2O$ molecule on Pd(111).

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